

Silicon Carbide Diode 5 January 2017

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quic	k reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 59 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	-	8	A
Tj	junction temperature		-	-	175	°C
Static charac	cteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
Dynamic cha	aracteristics					

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _r	recovered charge	$ I_F = 8 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; V_R = 400 \text{ V}; \\ T_j = 25 \text{ °C}; \text{ Fig. 7} $	-	13	-	nC

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	٦	K – K – A
2	А	anode	₀ O ₀	001aaa020
mb	n.c.	mounting base; isolated	TO220F-2L	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
NXPSC08650X	-	Plastic single-ended through-hole package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F	TO220F-2L				

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	650	V
V _{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 59 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 59 \ ^\circ C;$ squarewave pulse	-	16	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	48	А
for	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	-	385	A
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

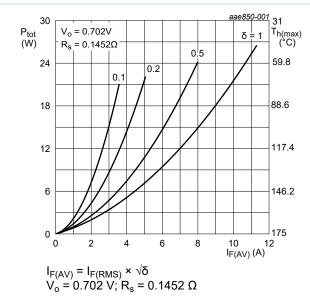
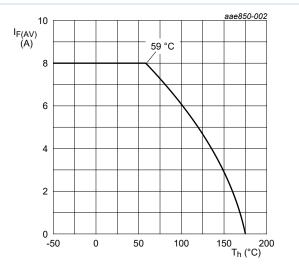


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

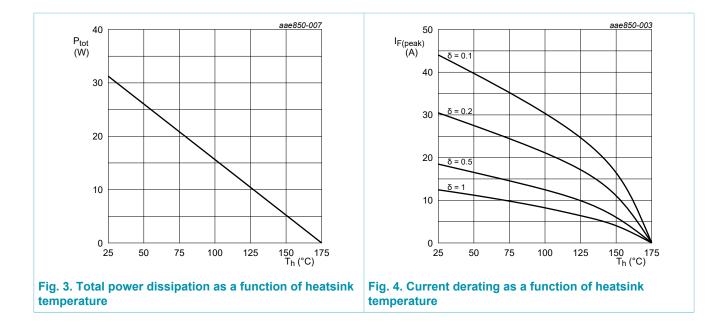




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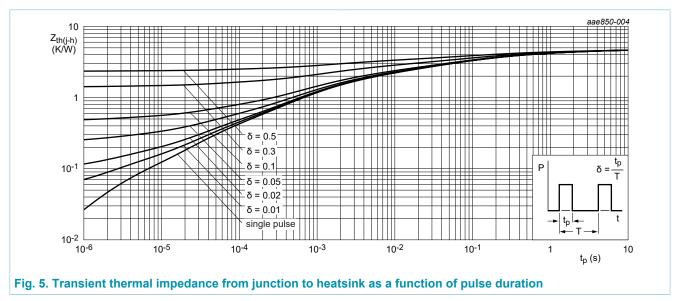


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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



9. Isolation characteristics

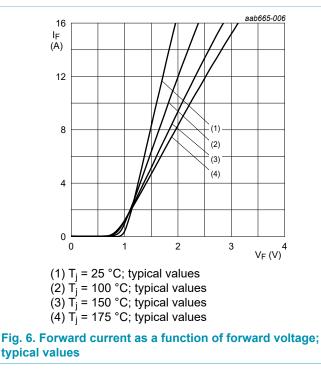
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; T _h = 25 °C; RH = 65 %	-	-	2500	V

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10. Characteristics

Table 7. Cha	aracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	-	230	μA
		V _R = 650 V; T _j = 150 °C	-	-	700	μA
Dynamic ch	naracteristics					
Qr	recovered charge	I _F = 8 A; dI _F /dt = 500 A/µs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>	-	13	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	260	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	30	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	24	-	pF



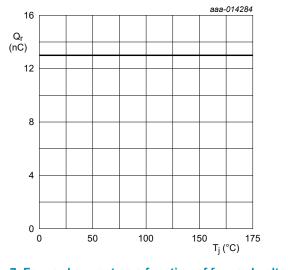


Fig. 7. Forward current as a function of forward voltage; typical values

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11. Package outline

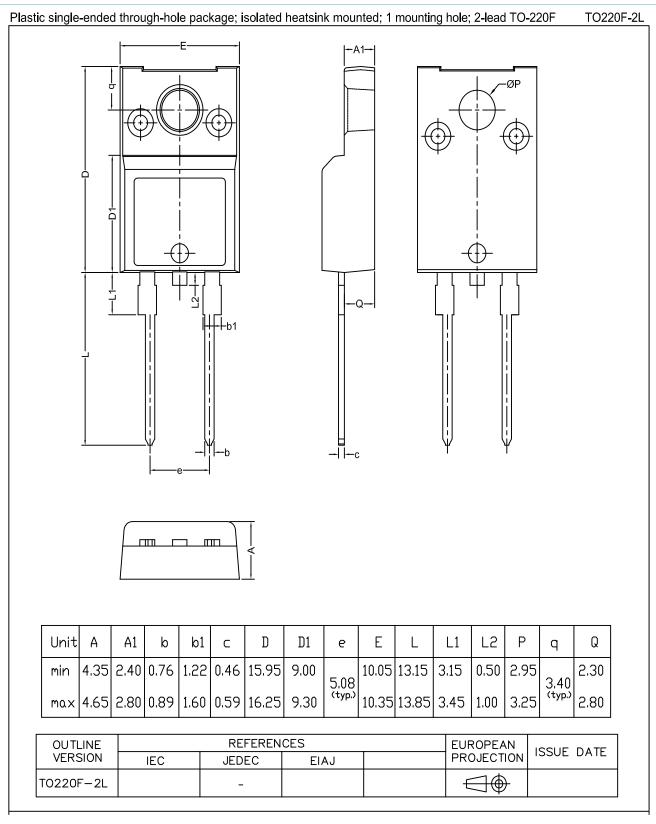


Fig. 8. Package outline TO220F-2L

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12. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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